WSP4626

N-Ch and P-Channel MOSFET

General Description

The WSP4626 is the highest performance trench N-ch and P-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSP4626 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

Product Summery

BVDSS	RDSON	ID
20V	21mΩ	6.7A
-20V	48mΩ	-4.4A

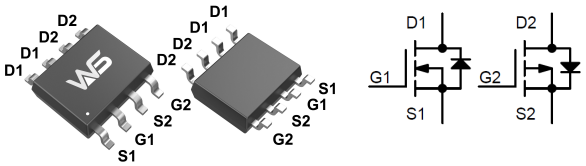
Applications

- MB/NB/UMPC/VGA
- DC-DC Power System
- Inverter

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

SOP-8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		N-Ch	P-Ch	
V_{DS}	Drain-Source Voltage	20	-20	V
V_{GS}	Gate-Source Voltage	±10	±12	V
I_D@T_A=25℃	Continuous Drain Current	6.7	-4.4	A
I_D@T_A=70℃	Continuous Drain Current	5.3	-3.5	A
I_{DM}	Pulsed Drain Current	20	-20	A
P_D@T_A=25℃	Total Power Dissipation	2.0	2.0	W
T_{STG}	Storage Temperature Range	-55 to 150	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R_{thJA}	Thermal Resistance Junction-Ambient	---	62.5	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	20	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=4.5V , I_D=6A	---	21	28	mΩ
		V_{GS}=2.5V , I_D=5.2A	---	28	38	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	0.4	0.72	1.2	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=20V , V_{GS}=0V .	---	---	1	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
Q_g	Total Gate Charge	V_{DS}=10V,V_{GS}=4.5V,I_D=6.5A.	---	10	---	nC
Q_{gs}	Gate-Source Charge		---	1.4	---	
Q_{gd}	Gate-Drain Charge		---	3.2	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=15V,V_{GS}=4.5V,R_G=6Ω, I_D=1A .	---	14	---	ns
T_r	Rise Time		---	10	---	
$T_{d(off)}$	Turn-Off Delay Time		---	34	---	
T_f	Fall Time		---	11	---	
C_{iss}	Input Capacitance	V_{DS}=15V,V_{GS}=0V,f=1MHz .	---	910	---	pF
C_{oss}	Output Capacitance		---	230	---	
C_{rss}	Reverse Transfer Capacitance		---	163	---	
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	2.6	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=1A.	---	---	1.2	V

P-Channel Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-20	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-4.5V , I_D=-5A	---	48	65	mΩ
		V_{GS}=-2.5V , I_D=-3A	---	62	85	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-0.4	-0.68	-1.2	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-20V , V_{GS}=0V , T_J=25℃	---	---	1	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±12V , V_{DS}=0V	---	---	±100	nA
Q_g	Total Gate Charge	V_{DS}=-10V,V_{GS}=-4.5V,I_D=-4A.	---	11.5	---	nC
Q_{gs}	Gate-Source Charge		---	3.5	---	
Q_{gd}	Gate-Drain Charge		---	3.3	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-10V,V_{GS}=-4.5V ,R_G=3Ω, I_D=-4A .	---	22	---	ns
T_r	Rise Time		---	15.7	---	
$T_{d(off)}$	Turn-Off Delay Time		---	59	---	
T_f	Fall Time		---	5.5	---	
C_{iss}	Input Capacitance	V_{DS}=-10V,V_{GS}=0V , f=1MHz.	---	1415	---	pF
C_{oss}	Output Capacitance		---	134	---	
C_{rss}	Reverse Transfer Capacitance		---	102	---	
I_S	Continuous Source Current	T_A =25°C	---	---	-2.4	A
V_{SD}	Diode Forward Voltage	I_{SD}= -1A , V_{GS}=0V.	---	---	-1.2	V

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the t≤ 10s junction to ambient thermal resistance rating.

N-Channel Typical Characteristics

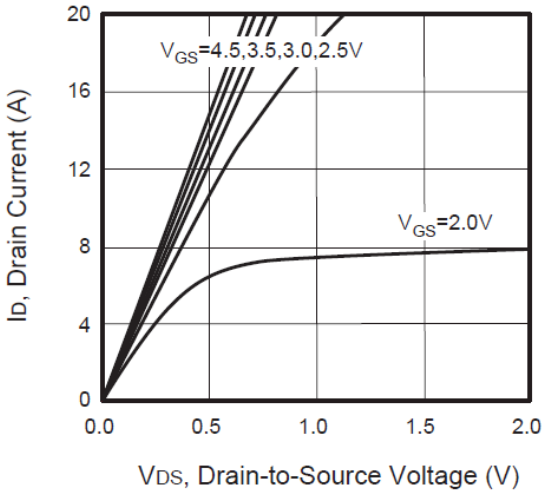


Figure 1. Output Characteristics

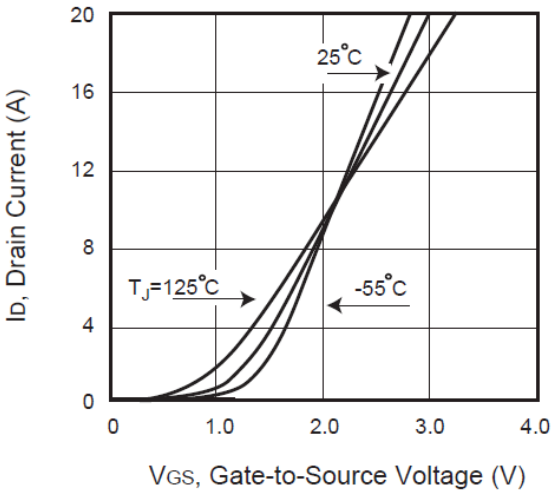


Figure 2. Transfer Characteristics

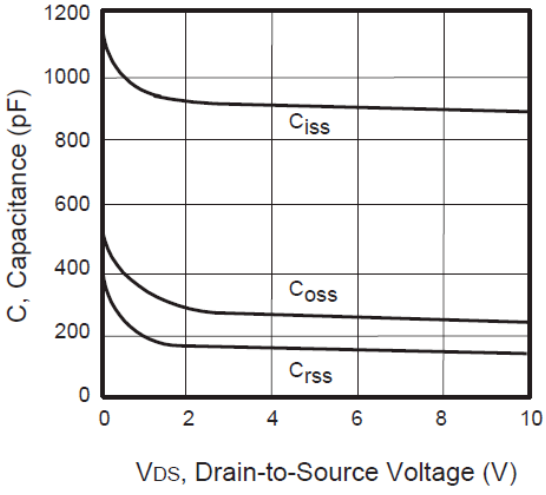


Figure 3. Capacitance

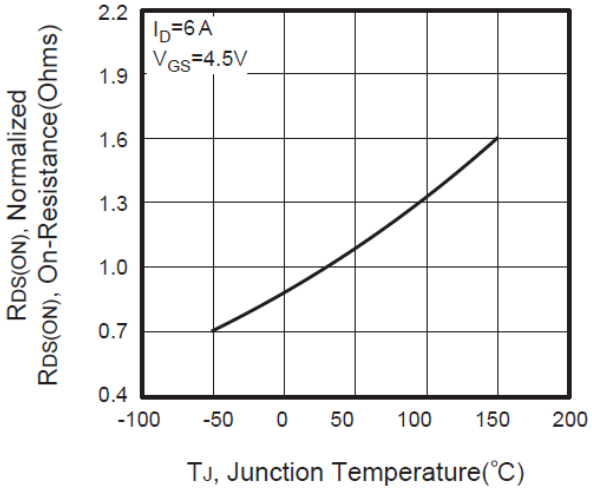


Figure 4. On-Resistance Variation with Temperature

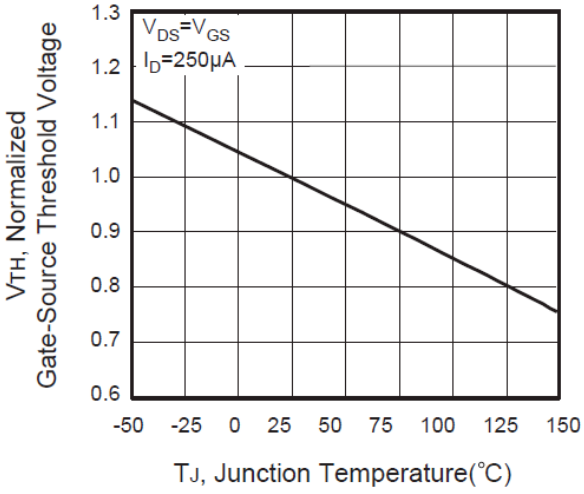


Figure 5. Gate Threshold Variation with Temperature

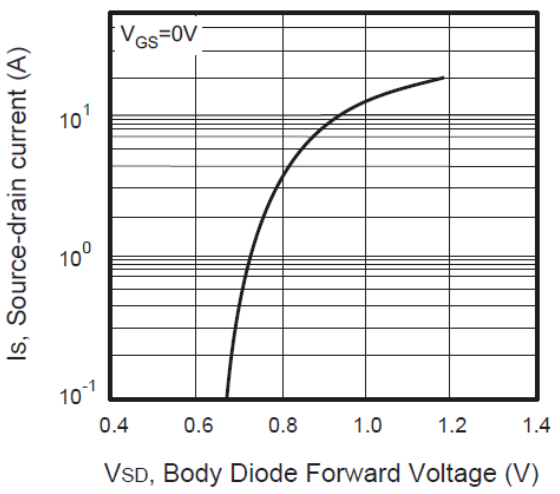


Figure 6. Body Diode Forward Voltage Variation with Source Current

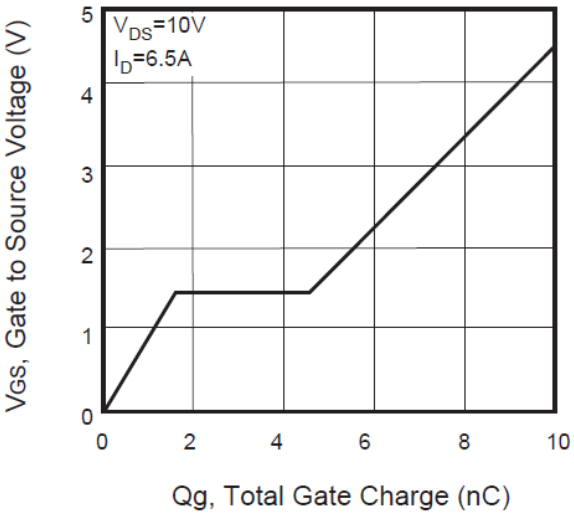


Figure 7. Gate Charge

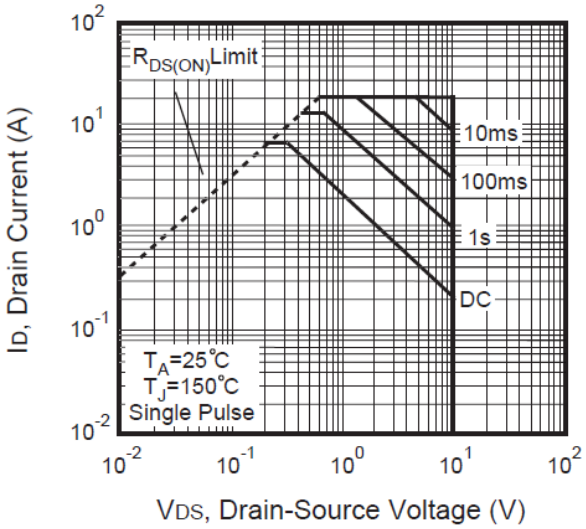


Figure 8. Maximum Safe Operating Area

P-Channel Typical Characteristics

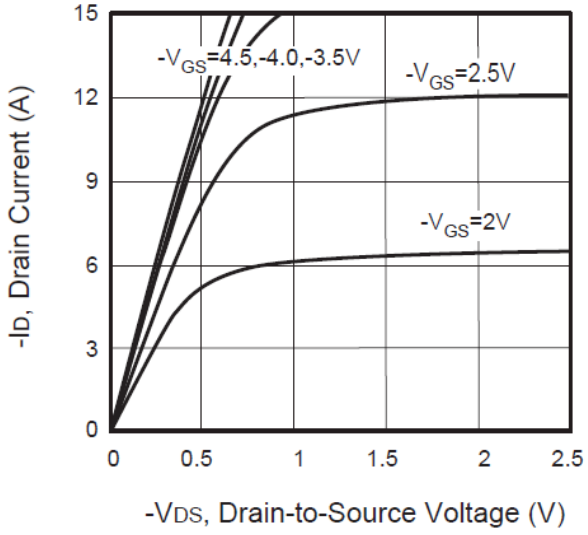


Figure 9. Output Characteristics

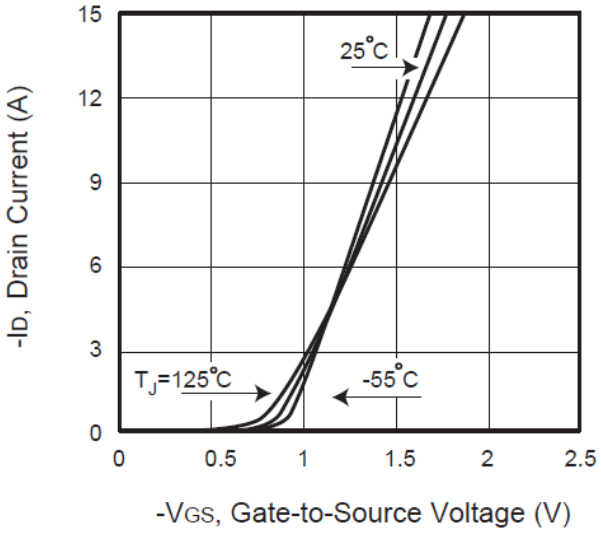


Figure 10. Transfer Characteristics

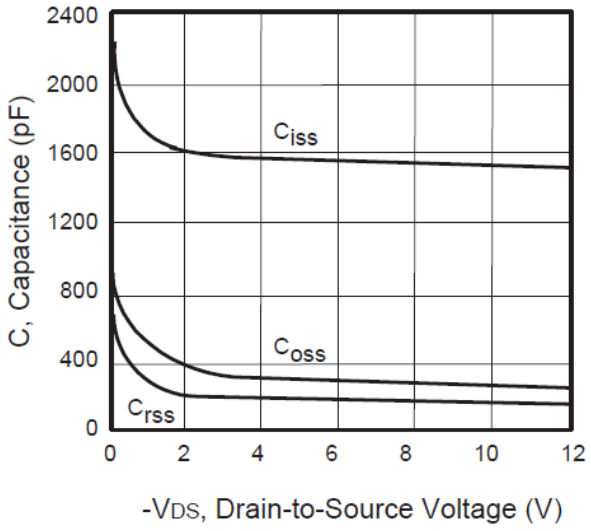


Figure 11. Capacitance

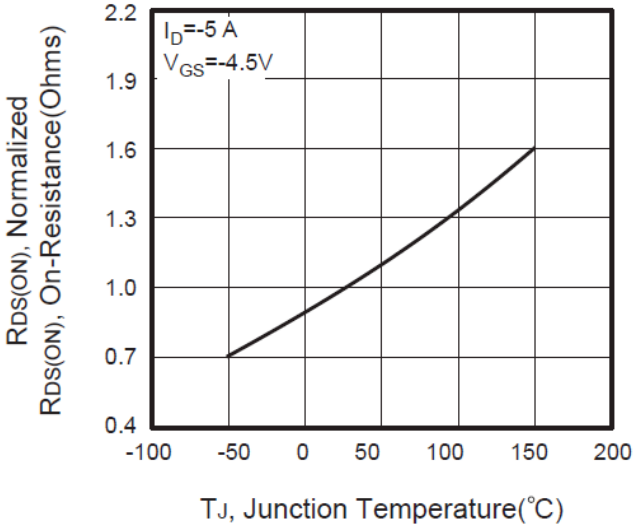


Figure 12. On-Resistance Variation with Temperature

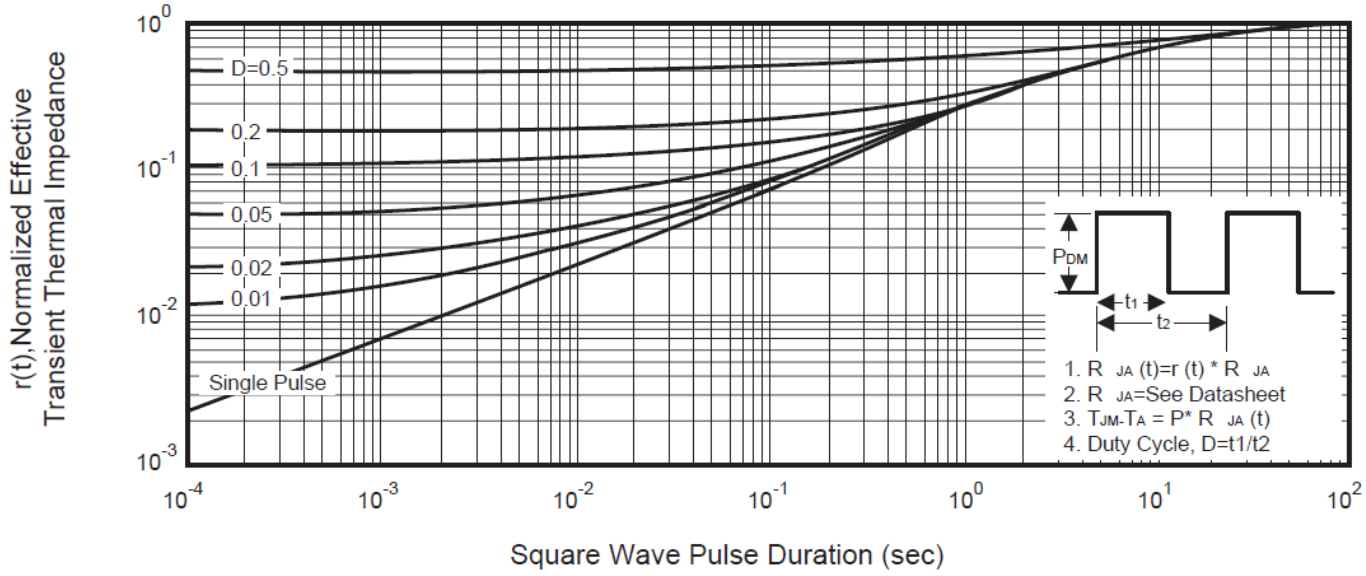


Figure 19. Normalized Thermal Transient Impedance Curve

Attention

1, Any and all Winsok power products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your Winsok power representative nearest you before using any Winsok power products described or contained herein in such applications.

2,Winsok power assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all Winsok power products described or contained herein.

3, Specifications of any and all Winsok power products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

4, Winsok power Semiconductor CO., LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

5,In the event that any or all Winsok power products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

7, Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. Winsok power believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

8, Any and all information described or contained herein are subject to change without notice due to product/technology improvement,etc. When designing equipment, refer to the "Delivery Specification" for the Winsok power product that you Intend to use.

9, this catalog provides information as of Sep.2014. Specifications and information herein are subject to change without notice.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET ***category:***

Click to view products by Winsok ***manufacturer:***

Other Similar products are found below :

IRFD120 JANTX2N5237 2SK2267(Q) BUK455-60A/B TK100A10N1,S4X(S MIC4420CM-TR VN1206L NDP4060 SI4482DY IRS2092STRPBF-EL IPS70R2K0CEAKMA1 SQM120N06-3M5L-GE3 TK31J60W5,S1VQ(O TK31J60W,S1VQ(O TK16J60W,S1VQ(O 2SK2614(TE16L1,Q) DMN1017UCP3-7 EFC2J004NUZTDG P85W28HP2F-7071 NTE2384 DMC2700UDMQ-7 DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7 STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 IPS60R360PFD7SAKMA1 DMN2990UFB-7B SSM3K35CT,L3F IPLK60R1K0PFD7ATMA1 2N7002W-G MCAC30N06Y-TP IPWS65R035CFD7AXKSA1 MCQ7328-TP SSM3J143TU,LXHF DMN12M3UCA6-7 PJMF280N65E1_T0_00201 PJMF380N65E1_T0_00201 PJMF280N60E1_T0_00201 PJMF600N65E1_T0_00201 PJMF900N65E1_T0_00201